

Features

- SiC MOSFET Technology
- High Speed Switching
- Reduction Of Heat Sink Requirements
- Essentially No Switching Losses
- Halogen Free. "Green" Device (Note 1)
- Lead Free Finish/RoHS Compliant("P" Suffix Designates RoHS Compliant. See Ordering Information) (Note2)

Maximum Ratings

- Operating Junction Temperature Range : -55°C to +175°C
- Storage Temperature Range: -55°C to +175°C
- Thermal Resistance Junction to Ambient,Max(Note 3): 62°C/W
- Thermal Resistance Junction to Case,Typ : 0.90°C/W

Applications

- Solar Inverters
- Uninterruptible Power Supply
- Photovoltaic Inverter
- Battery Chargers
- Motor Drives

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V _{DS}	1200	V
Gate-Source Voltage ^(Note 4)		V _{GSmax}	-10/+25	V
Gate-Source Voltage		V _{GSop}	-5/+20	V
Continuous Drain Current V _{GS} =20V	Tc=25°C	I _D	24	A
	Tc=110°C		16.5	
Pulsed Drain Current ^(Note 5)		I _{DM}	65	A
Total Power Dissipation	Tc=25°C	P _D	166	W
	Tc=110°C		71	
Avalanche Energy, Single Pulse	V _{DD} =100V, I _D =7A	E _{AS}	625	mJ

Note1:Halogen free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

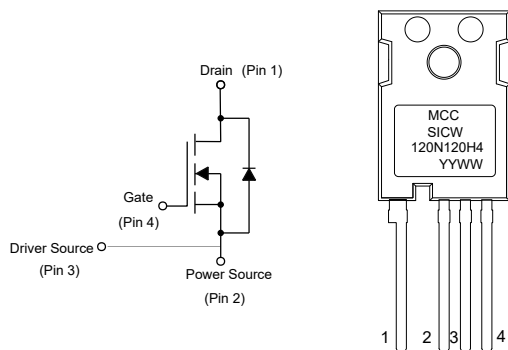
Note2:High Temperature Solder Exemptions Applied, see EU Directive Annex 7a.

Note3:Device in a still air environment with $T_A=25^{\circ}C$.

Note4:AC $f > 1Hz$, duty cycle < 1%

Note5:Pulse Test: Pulse Width Limited by T_{jmax} .

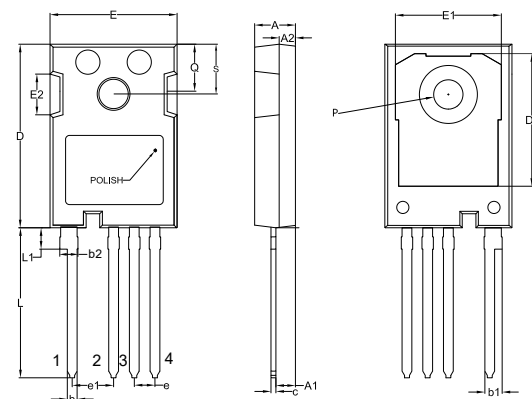
Internal Structure and Marking Code



Device Code: SICW120N120H4
Date Code: YYWW (Year & Week)

SiC N-CHANNEL MOSFET

TO-247-4



DIMENSIONS					
DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	0.189	0.205	4.80	5.20	
A1	0.090	0.098	2.29	2.50	
A2	0.074	0.082	1.88	2.08	
b	0.043	0.054	1.10	1.36	
b1	0.093	0.108	2.35	2.75	
b2	0.094	0.112	2.39	2.84	
c	0.022	0.028	0.55	0.70	
D	0.917	0.929	23.30	23.60	
D1	0.640	0.663	16.25	16.85	
E	0.620	0.632	15.75	16.05	
E1	0.543	0.559	13.80	14.20	
E2	0.173	0.201	4.4	5.10	
e	0.100		2.54		
e1	0.199		5.06		
L	0.683	0.694	17.34	17.64	
L1	0.157	0.169	4.00	4.30	
P	0.138	0.148	3.51	3.75	Φ
Q	0.220	0.236	5.60	6.00	
S	0.220	0.248	5.60	6.30	

Electrical Characteristics @ $T_J=25^{\circ}\text{C}$ (Unless Otherwise Specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit	
Static Characteristics							
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =100μA	1200			V	
Gate-Source Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =20V			250	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =1200V, V _{GS} =0V			50	μA	
Gate-Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =10mA	2	2.95	4.5	V	
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =20V, I _D =10A		120	160	mΩ	
		V _{GS} =20V, I _D =10A, T _J =175°C		200		mΩ	
Internal Gate Resistance	R _g	f=1MHz, V _{AC} =25mV		1.8		Ω	
Transconductance	g _{FS}	V _{DS} =12.5V, I _D =60A		6.2		S	
Dynamic Characteristics							
Input Capacitance	C _{iss}	V _{DS} =800V, V _{GS} =0V, f=1MHz, V _{AC} =25mV		1083		pF	
Output Capacitance	C _{oss}			56			
Reverse Transfer Capacitance	C _{rss}			8			
Coss Stored Energy	E _{oss}				23		μJ
Total Gate Charge	Q _g	V _{DS} =800V, V _{GS} =-5/+20V, I _D =10A		67		nC	
Gate-Source Charge	Q _{gs}			14.5			
Gate-Drain Charge	Q _{gd}			29			
Turn-On Delay Time	t _{d(on)}	V _{DD} =800V, V _{GS} =0/+20V, R _G =10Ω, I _D =8A, R _L =100Ω		24		ns	
Rise Time	t _r			24			
Turn-Off Delay Time	t _{d(off)}			34			
Fall Time	t _f			33			
Turn-On switching energy	E _{on}	V _{DD} =800V, V _{GS} =0/+20V, R _G =2.7Ω, I _D =10A		13		μJ	
Turn-Off switching energy	E _{off}			19			
Diode Characteristics							
Continuous Body Diode Current	I _S	V _{GS} =0V, T _C =25°C		25		A	
Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _{SD} =2.5A		3.4		V	
Reverse Recovery Time	t _{rr}	V _{GS} =0V, I _{SD} =10A, V _{DS} =400V, dI _F /dt=300A/μs		53		ns	
Reverse Recovery Charge	Q _{rr}				63		nC
Peak Reverse Recovery Current	I _{rrm}				2.25		A

Curve Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Fig. 1 - Typical Output Characteristic ($T_J = 25^\circ\text{C}$)

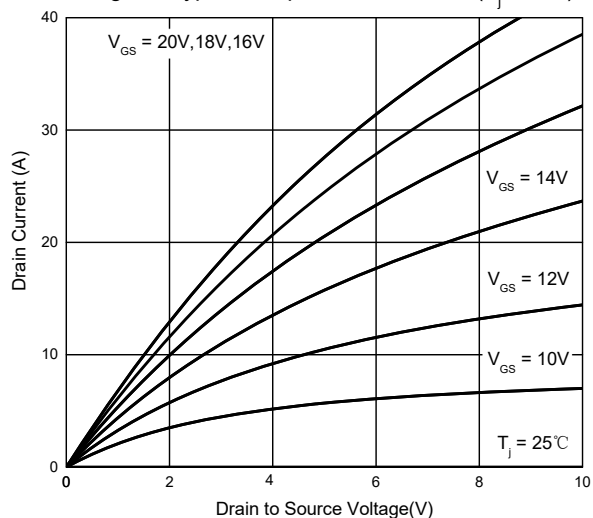


Fig. 2 - Typical Output Characteristic ($T_J = 175^\circ\text{C}$)

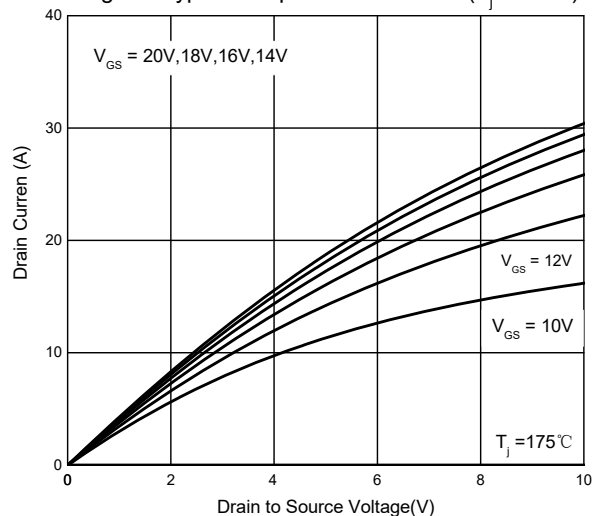


Fig. 3 - On-Resistance vs. Drain Current

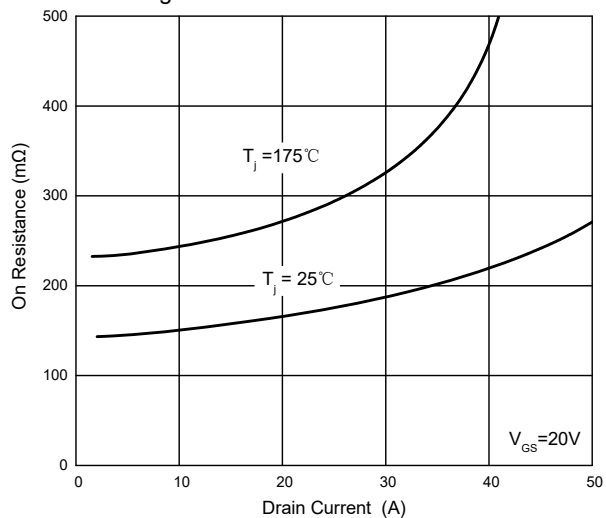


Fig. 4 - Typical Transfer Characteristic

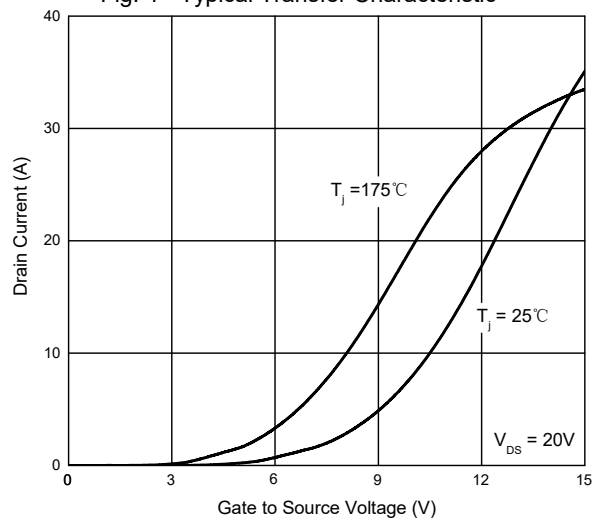


Fig. 5 - On-Resistance vs. Gate Voltage

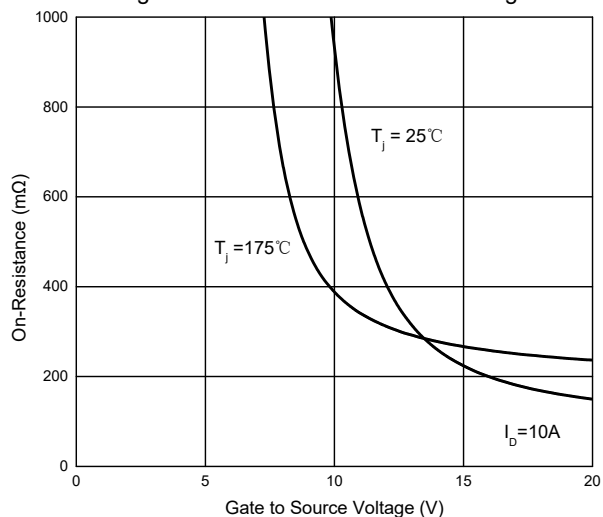
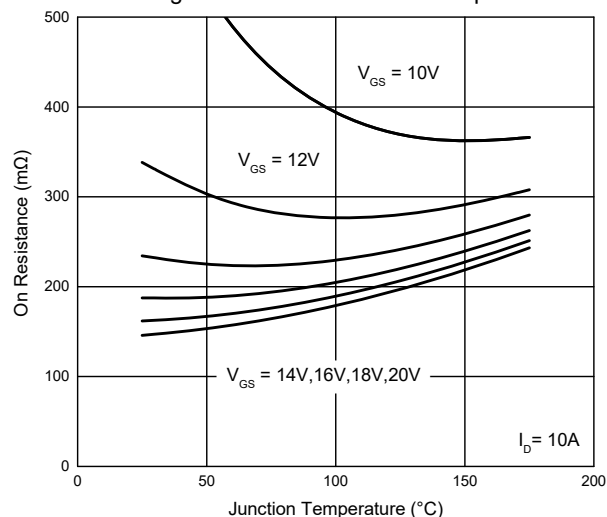


Fig. 6 - On-Resistance vs. Temperature



Curve Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Fig. 7 - Normalized On-Resistance vs. Temperature

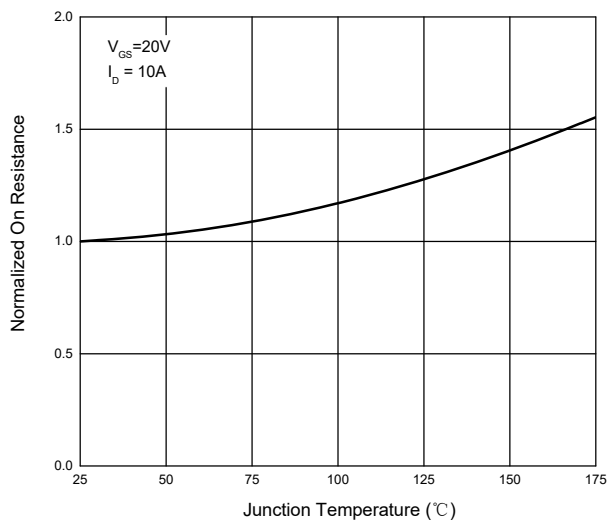


Fig. 8 - Reverse Output Voltage

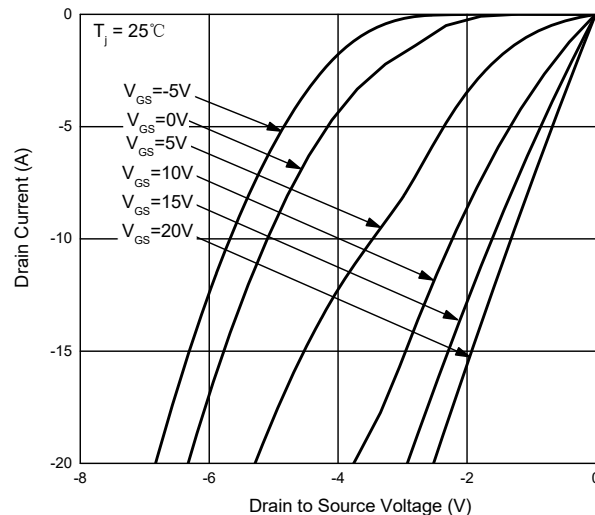


Fig. 9 - Reverse Output Voltage

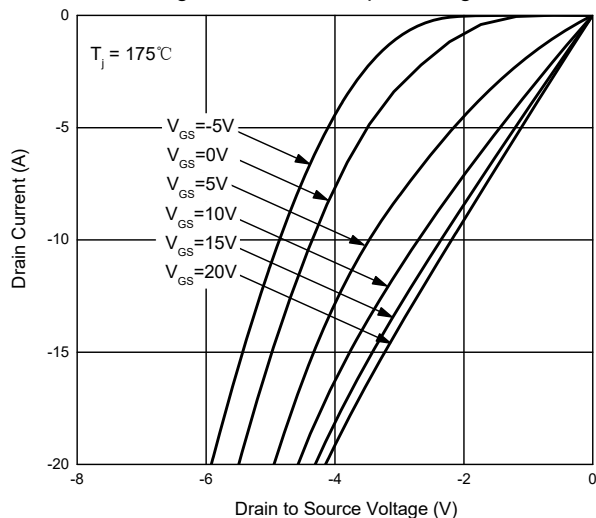


Fig. 10 - Capacitances vs. V_{DS}

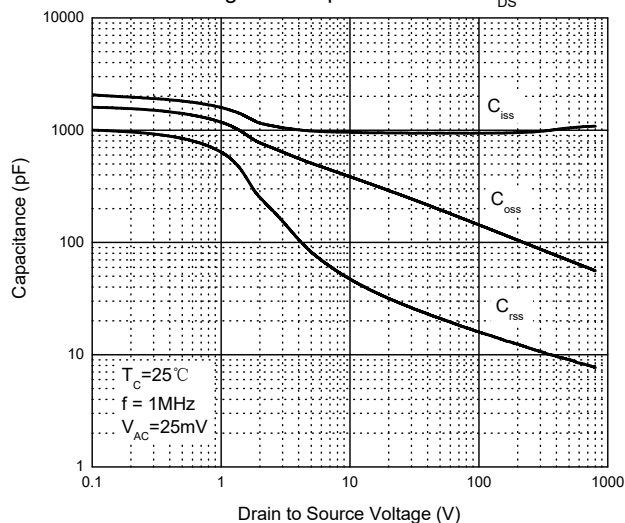


Fig. 11 - Threshold Voltage vs. Temperature

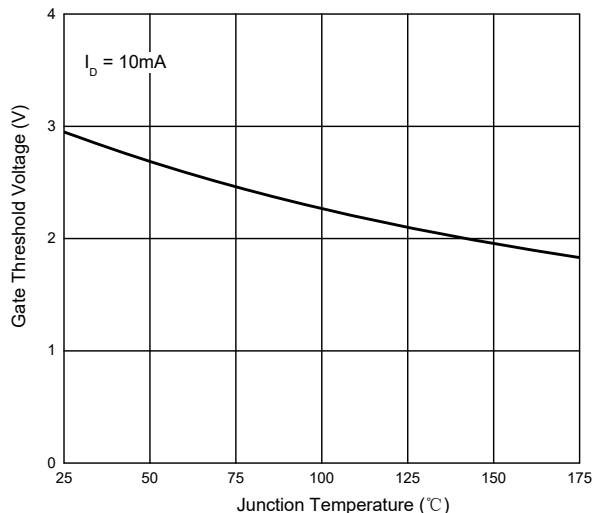
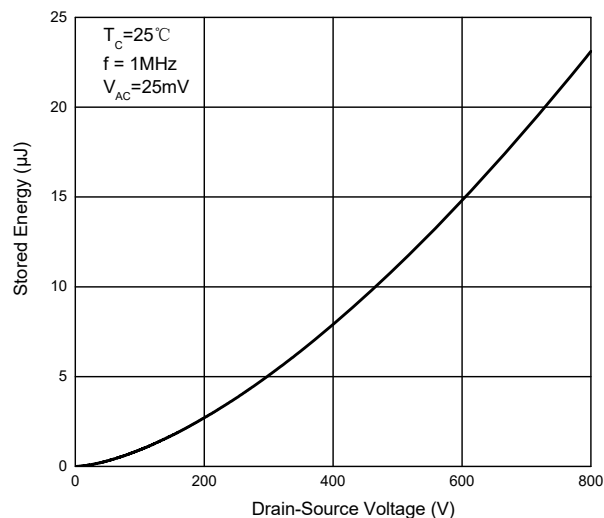


Fig. 12 - Output Capacitor Stored Energy



Curve Characteristics ($T_J=25^\circ\text{C}$ unless otherwise specified)

Fig. 13 - Power Derating

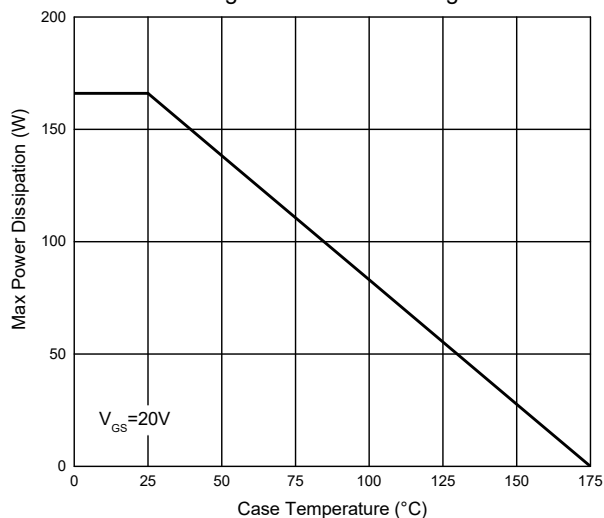


Fig. 14 - Drain Current Derating

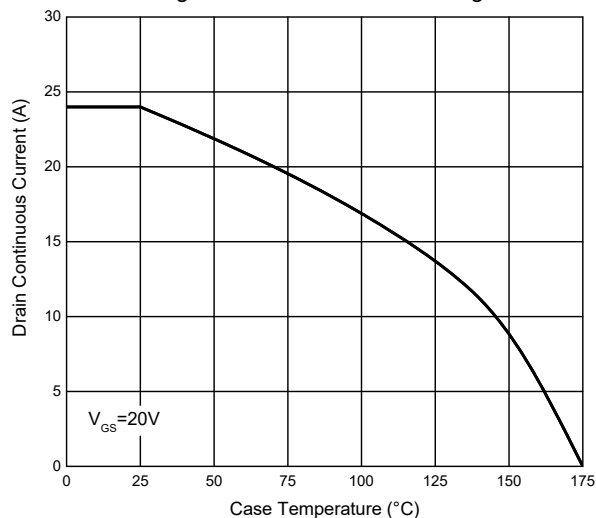


Fig. 15 - Safe Operation Area

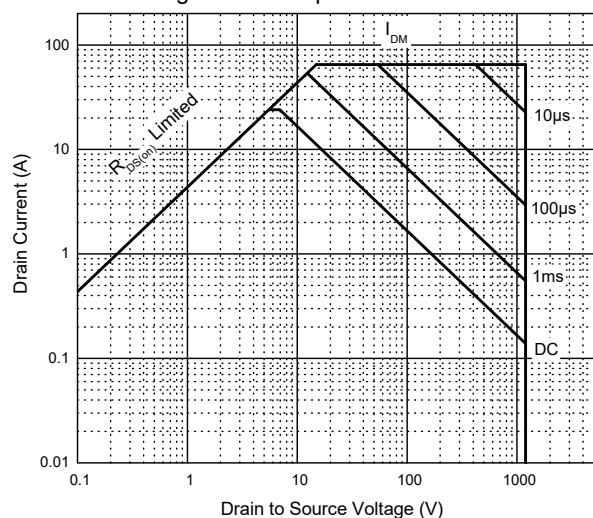


Fig. 16 - Typical Gate Charge

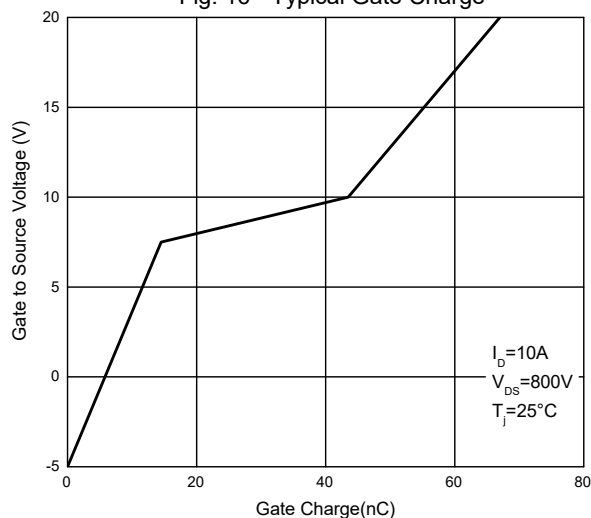


Fig. 17 - Clamped Inductive Switching Energy vs. Drain Current

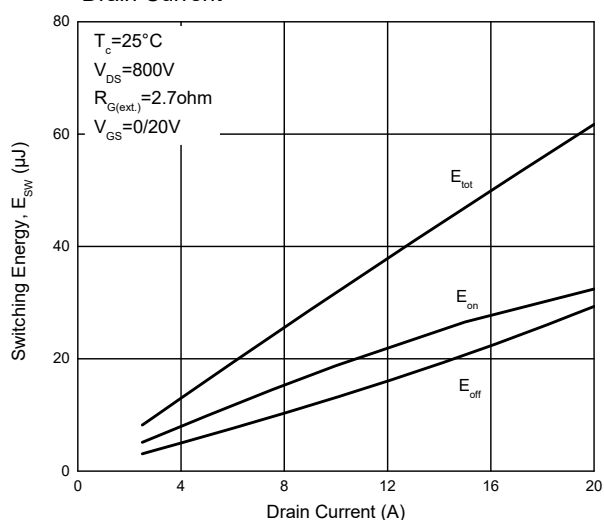
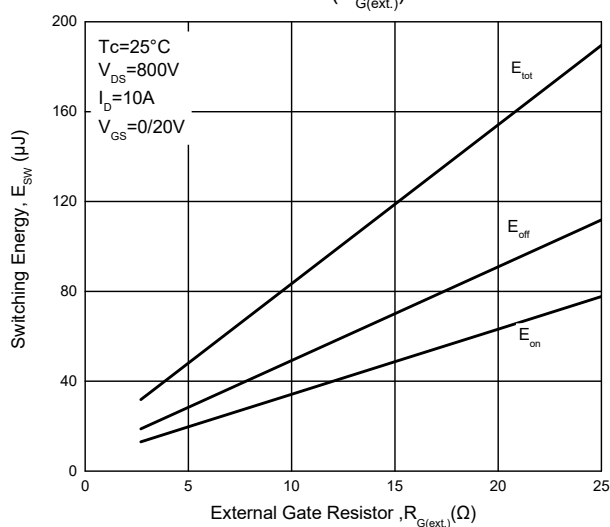
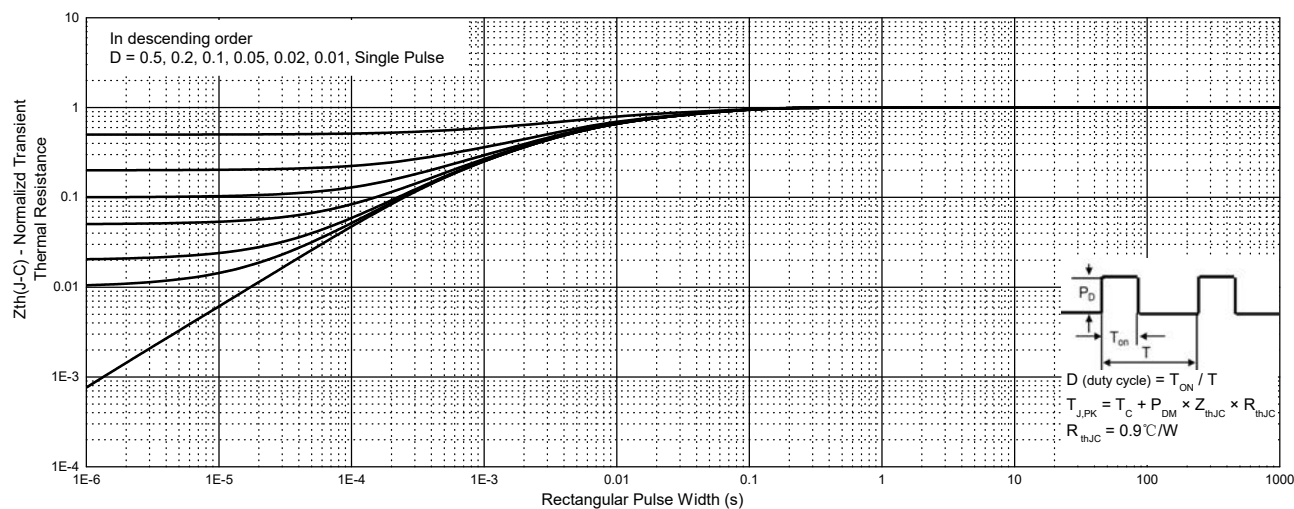


Fig. 18 - Clamped Inductive Switching Energy vs. External Gate Resistor ($R_{G(ext.)}$)



Curve Characteristics (T_J=25 °C unless otherwise specified)

Fig.19 - Normalized Transient Thermal Impedance



Ordering Information

Device	Packing
SICW120N120H4-BP	Tube:30pcs/Tube, 1.8K/Ctn;

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